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## Claims

 A method of improving current density for a carbon nanotube(CNT) emitter source, said method comprising the steps of:

forming a CNT layer by screen-printing a CNT paste through a patterned mesh onto substrate, wherein a plurality of conductive pattern is formed thereon so as to form emitter pixel array;

performing a soft bake process to said substrate; performing a sintering process; and performing a taping process.

2. The method according to claim 1, wherein step of performing a taping process comprises the steps of

forming a adhesive film on said substrate; and pulling said adhesive film up and striping away so as to poor bonding of CNT layer.

- The method according to claim 1, after soft bake step further comprising performing a taping process to further increase said current density in the same electric field intensity.
- 4. The method according to claim 2, wherein step of said forming an adhesive film on said substrate is performed by laminator.
- 5. The method according to claim 2, wherein step of said forming a adhesive film on said substrate is performed by printing a film and then scraping said film.

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- 6. The method according to claim 2, wherein step of said forming a adhesive film on said substrate is performed by attaching said adhesive film manually on said substrate and then rubbing said adhesive film.
- 7. The method according to claim 2, wherein said adhesive film to remove said organic is through physical or electric static attracting process.
  - 8. The method according to claim 2, wherein said adhesive film comprises a plastic film with adherent material thereon.
  - 9. The method according to claim 2, wherein said adhesive film comprises a tape without adherent material but can attach on said CNT layer by electric static force.
  - 10. The method according to claim 1, wherein said step of performing said soft bake process is done at a temperature of about 50-200  $^{\circ}$ C.
  - 11. The method according to claim 1, wherein said step of performing said sintering process is done at a temperature of about 350-550  $^{\circ}$ C.